

49. (New) The method of claim 5, wherein preparing the substrate comprises forming a PWELL in an *n*-type substrate.
50. (New) The method of claim 5, wherein forming the first gate structure including the PWELL without using the mask comprises forming the PWELL by a blanket implant of boron ions at about 430 keV.
51. (New) The method of claim 5, wherein forming the first gate structure including the PWELL without using the masking comprises forming the PWELL having a depth of about 200 nanometers.
52. (New) The method of claim 5, wherein forming the first gate structure including the PWELL without using the masking comprises forming the PWELL having a blanket implant of boron ions at about 430 keV and a depth of about 200 nanometers.
53. (New) The method of claim 49, wherein forming the first gate structure including the PWELL without using the mask comprises forming the PWELL by a blanket implant of boron ions at about 430 keV.
54. (New) The method of claim 49, wherein forming the first gate structure including the PWELL without using the masking comprises forming the PWELL having a depth of about 200 nanometers.
55. (New) The method of claim 9, wherein preparing the substrate comprises forming a PWELL in an *n*-type substrate.
56. (New) A method comprising:  
preparing an *n*-type substrate;  
forming a first gate structure including only blanket implants; and